Abstract of the Disclosure

A GaN layer is grown on a sapphire substrate, an SiO_2 film is formed on the GaN layer, and a GaN semiconductor layer including an MQW active layer is then grown on the GaN layer and the SiO_2 film using epitaxial lateral overgrowth. The GaN based semiconductor layer is removed by etching except in a region on the SiO_2 film, and a p electrode is then formed on the top surface of the GaN based semiconductor layer on the SiO_2 film, to join the p electrode on the GaN based semiconductor layer to an ohmic electrode on a GaAs substrate. An n electrode is formed on the top surface of the GaN based semiconductor layer.